

FIG. 1

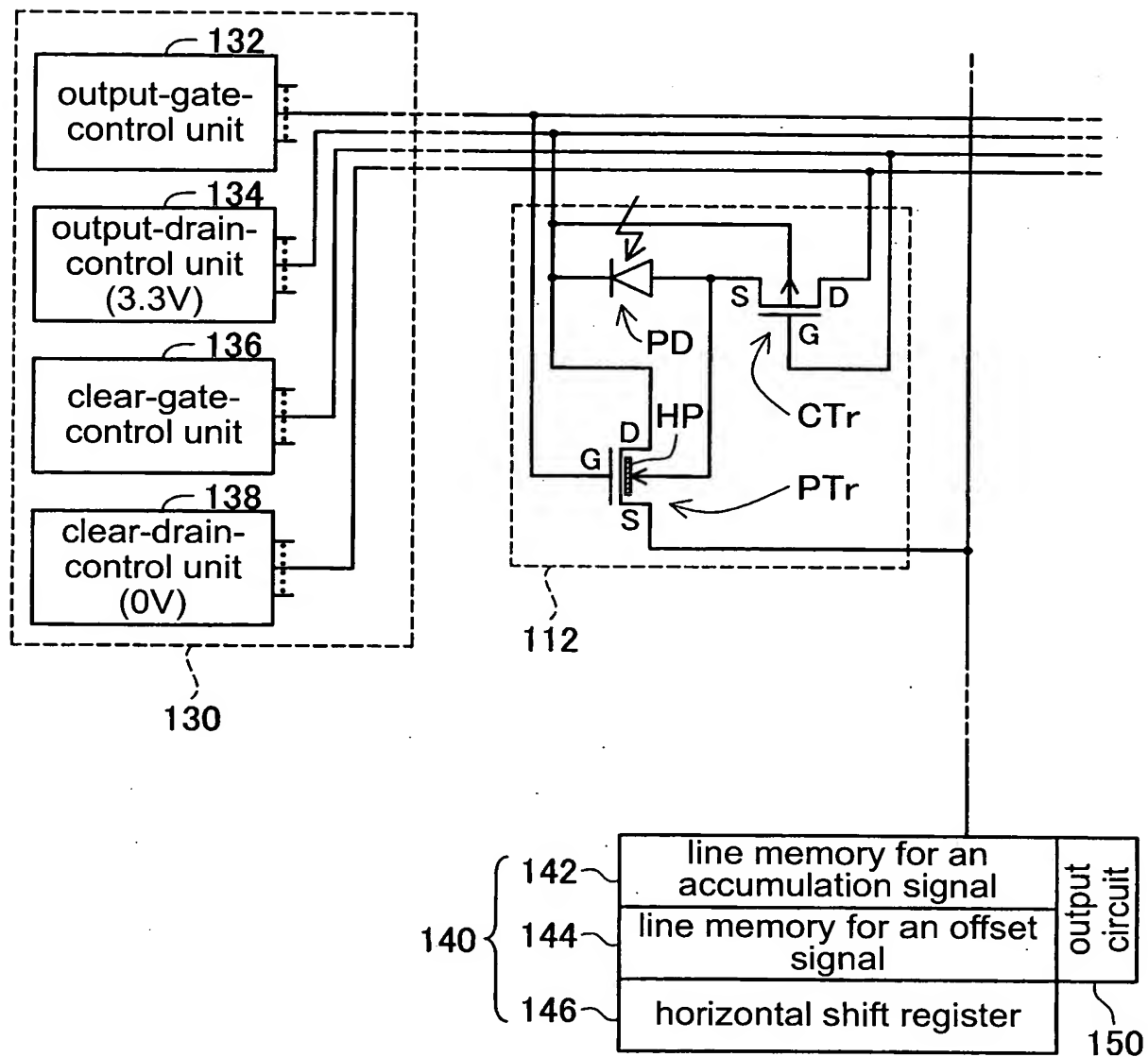


FIG. 2

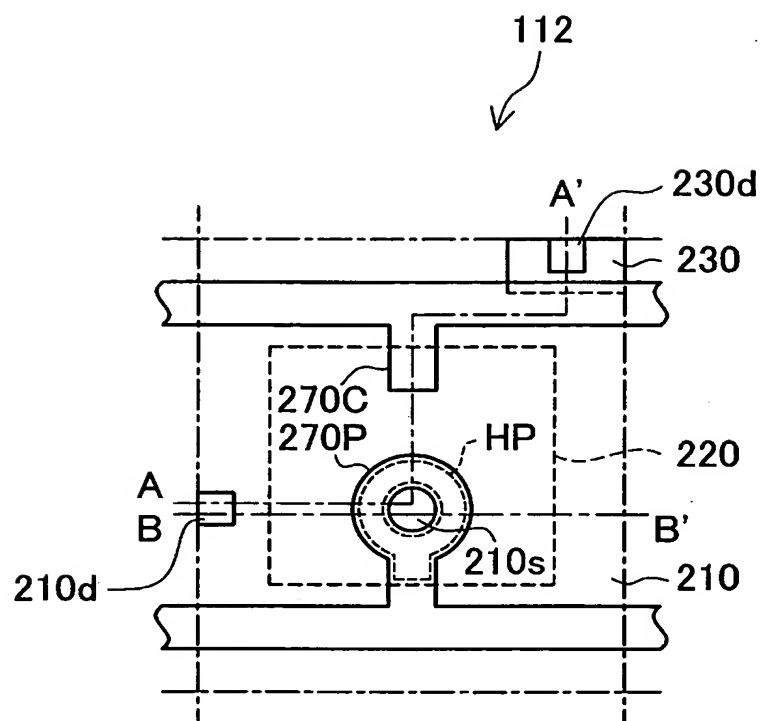


FIG. 3

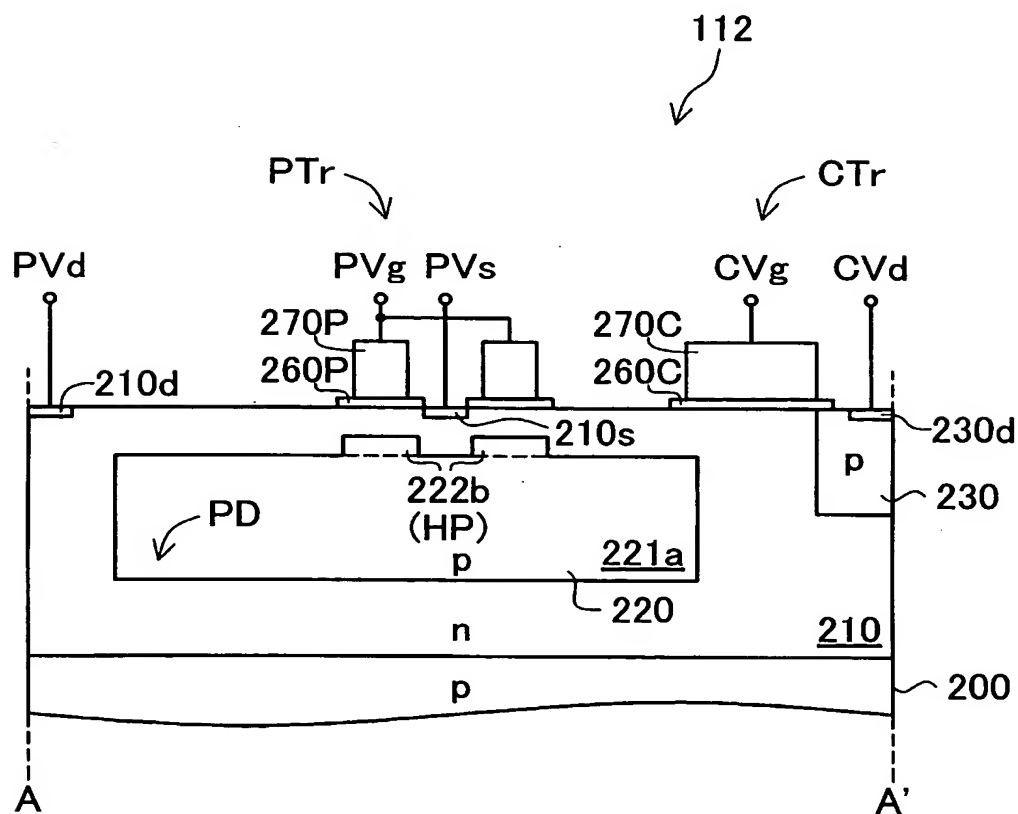


FIG. 4

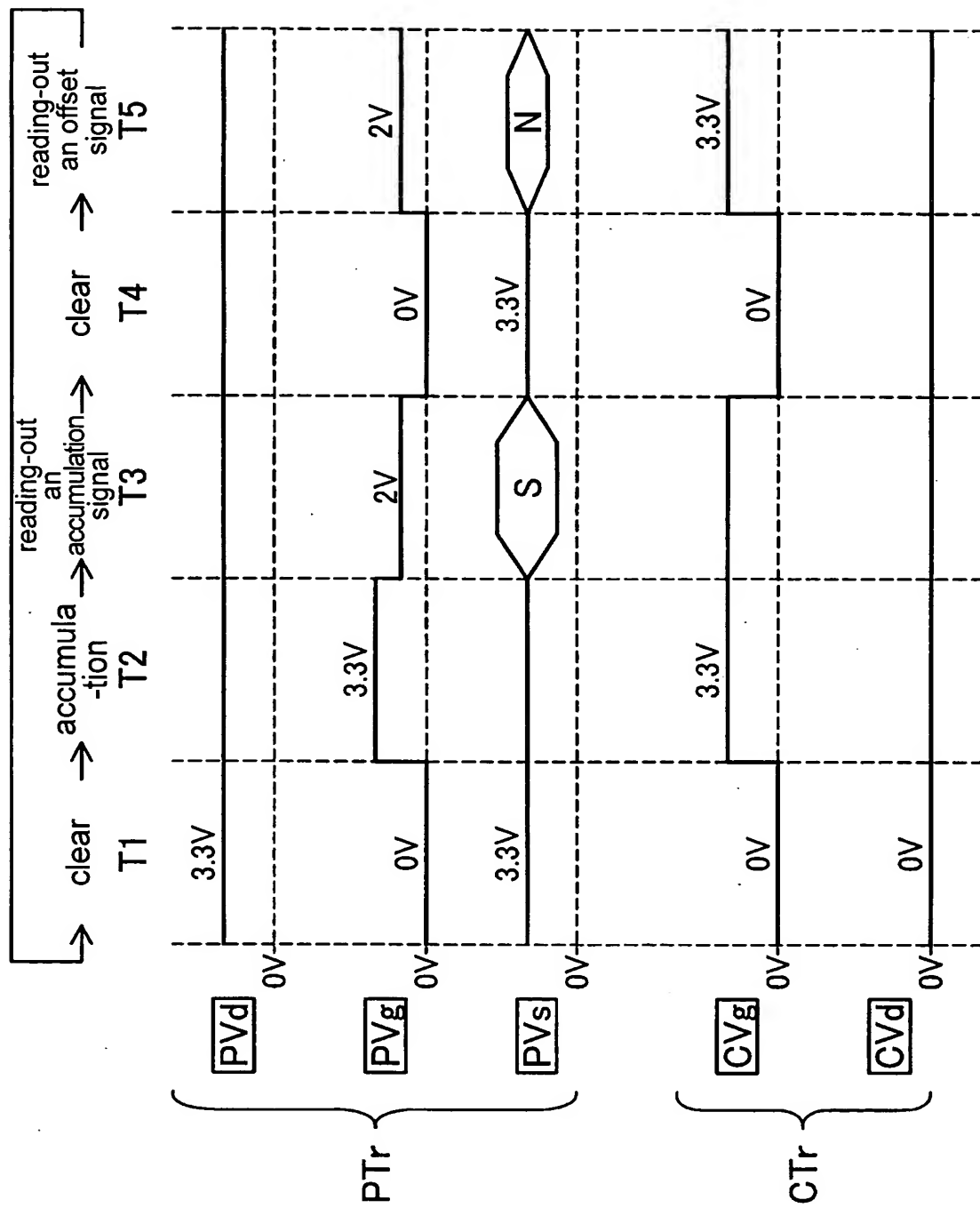


FIG. 5

[illegible]

FIG. 6

This cross-sectional view shows the device during an accumulation period. The structure includes a substrate 200 with a p-type region. A channel region 210 is formed above the substrate, containing an n-type region. A gate stack 210d is located on the left, connected to a 3.3V supply. A source region 220 is formed in the channel region, containing a p-type region. A drain region 230 is formed on the right, containing a p-type region. A gate stack 230d is located on the right, connected to a 0V supply. A gate stack 270P is located on the source region, connected to a 3.3V supply. A gate stack 270C is located on the drain region, connected to a 3.3V supply. A gate stack 112 is located on the drain region, connected to a 0V supply. Arrows indicate the flow of current from the source region 220 to the drain region 230. Labels include 3.3V, 0V, 210d, 270P, 270C, 112, PTr, CTr, 230d, p, 230, PD, HP, 220, n, 210, and 200.

FIG. 7

reading-out period

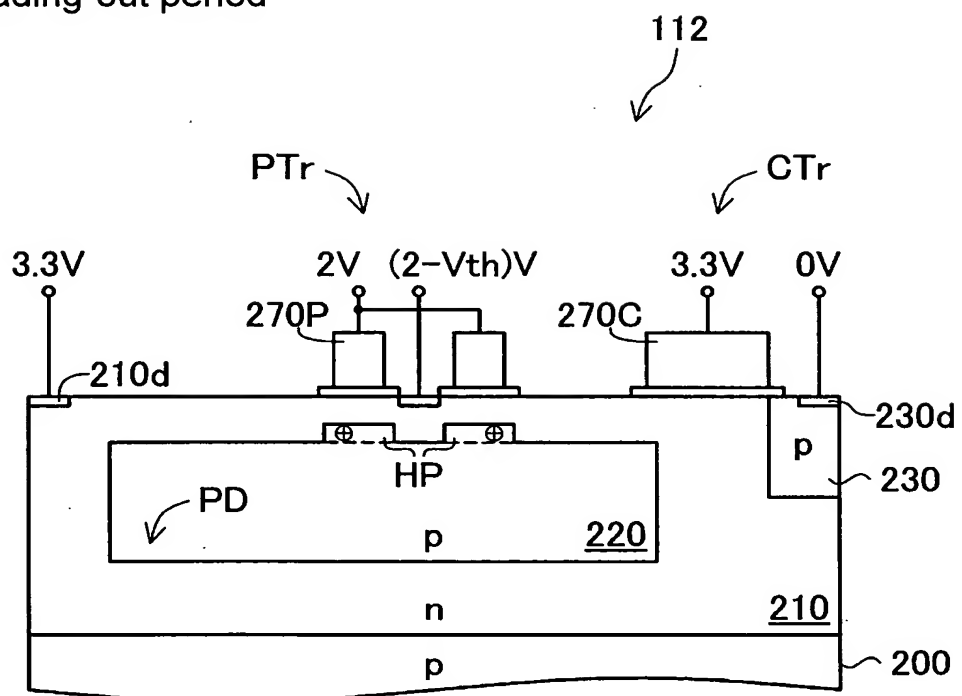


FIG. 8



[illegible]

FIG. 12A

[illegible]

FIG. 12B

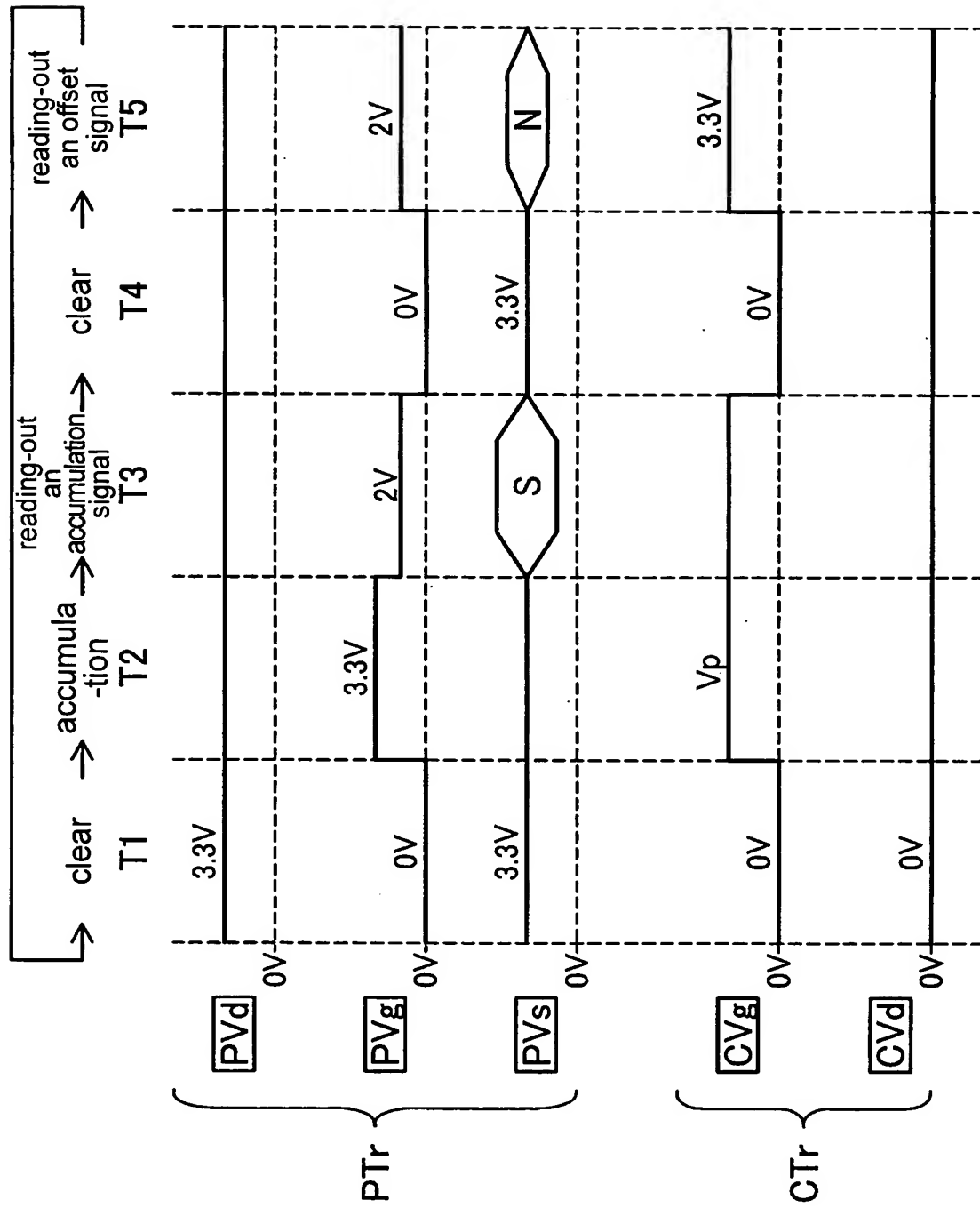
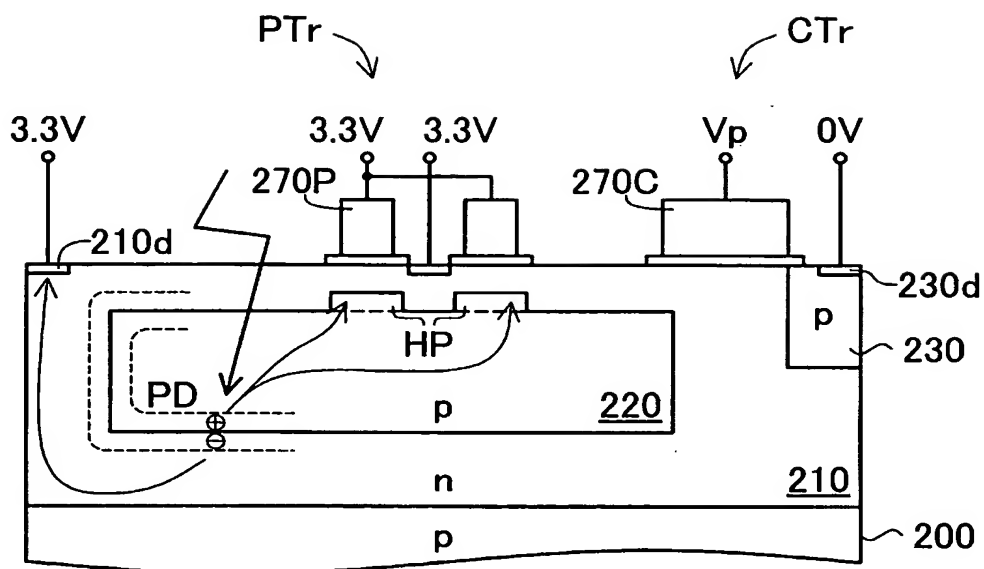


FIG.13

112



accumulation period

112

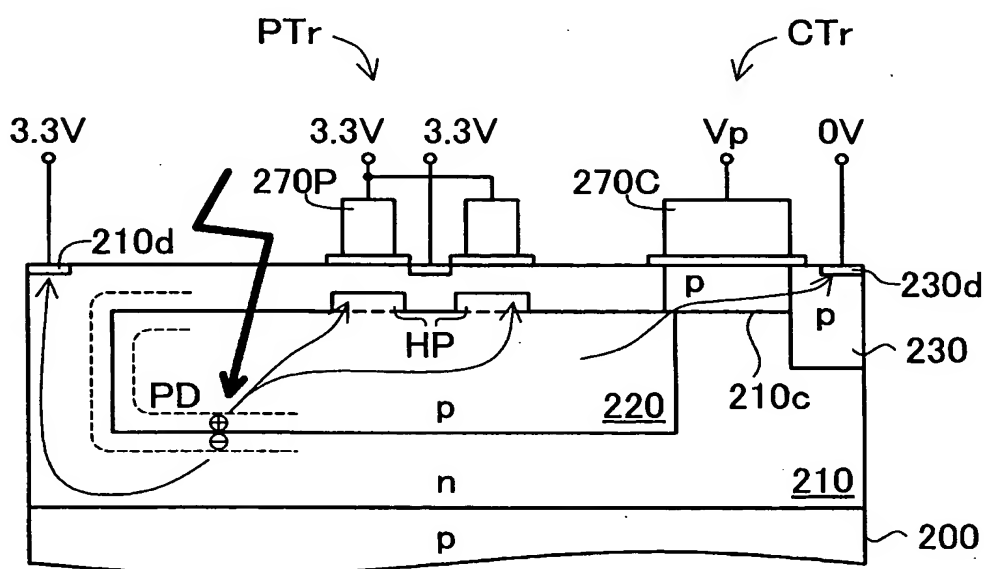


FIG.14B